

formed on said semiconductor substrate on regions of said semiconductor substrate other than a region above said light-receiving portion,

B1 end
wherein said solid-state imaging device is formed such that said light-shielding film has a multilayer structure including a first film formed of a film deposited by sputtering or vapor deposition and a second film deposited by chemical vapor deposition.

subcl
B2
21. (new) A solid state imaging device according to claim 1, wherein said first film has a thickness in a range of 20 to 100 nm, and said second film has a thickness in a range of about 80 nm to 200 nm so as to maintain a satisfactory light-shielding property.

22. (new) A solid-state imaging device according to claim 1, wherein the entirety of the light-shielding film is less than 200 nm.

23. (new) A solid-state imaging device according to claim 1, wherein the entirety of the light-shielding film is less than 200 nm.

24. (new) A solid-state imaging device according to claim 1, wherein the entirety of the light-shielding film is